

**Amendments to the Specification:**

Please replace the paragraph beginning at page 1, line 9, with the following rewritten paragraph:

-- This application is a continuation-in-part of U.S. Patent Application No. 09/812,535, filed March 19, 2001, entitled "In-Situ Detection of Thin-Metal Interface Using Optical Interference," and is related to U.S. Patent Application No. 09/976,442 (~~Attorney Docket No. LAM2P253.CIP1~~), filed October 12, 2001, entitled "In-Situ Detection of Thin-Metal Interface Using Optical Interference via a Dynamically updated Reference," both of which are incorporated herein by reference. --

Please replace the paragraph beginning at page 15, line 4, with the following rewritten paragraph:

-- Figure 4 is a flowchart showing a method 400 for detecting an endpoint during a chemical mechanical polishing process, in accordance with an embodiment of the present invention. In operation 402, broad band reflectance data is obtained by illuminating a portion of the surface of the wafer with a broad band light source. Reflected spectrum data is then received corresponding to the spectrums of light reflected from the illuminated portion of the surface of the wafer. In addition, during operation 402, the reflectance data used as a normalization reference can be updated, as described in greater detail in related U.S. Patent Application No. 09/976,442 (~~Attorney Docket No. LAM2P253.CIP1~~), filed October 12, 2001, entitled "In-Situ Detection of Thin-Metal Interface Using Optical Interference via a Dynamically updated Reference," which is incorporated by reference in its entirety. --